

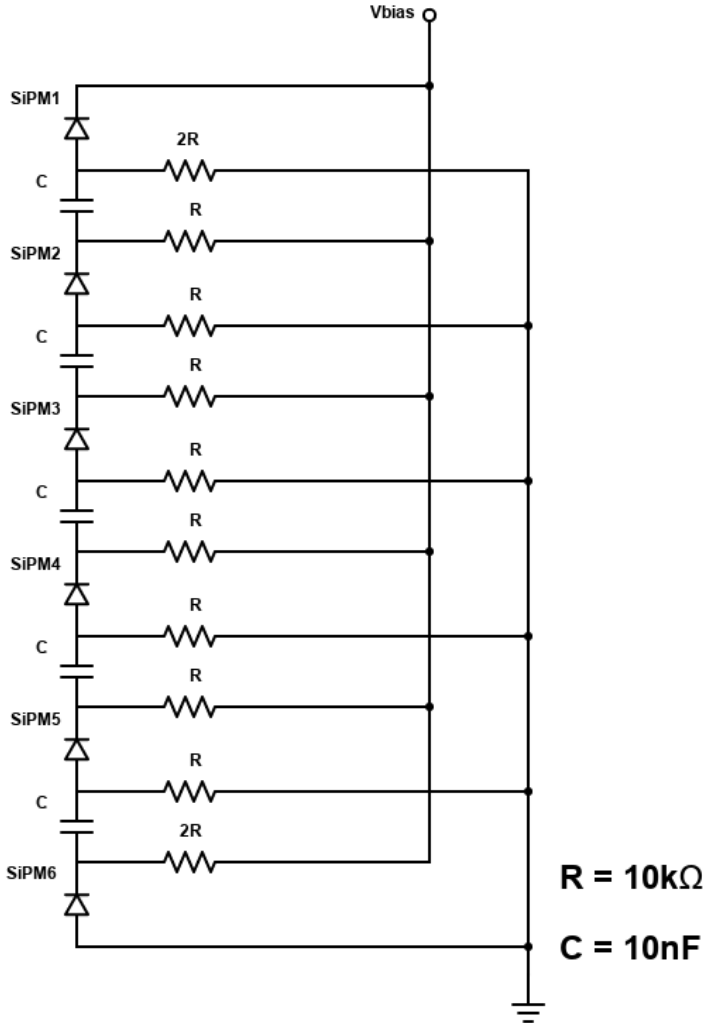
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# Series-Parallel SiPM bias Simulation

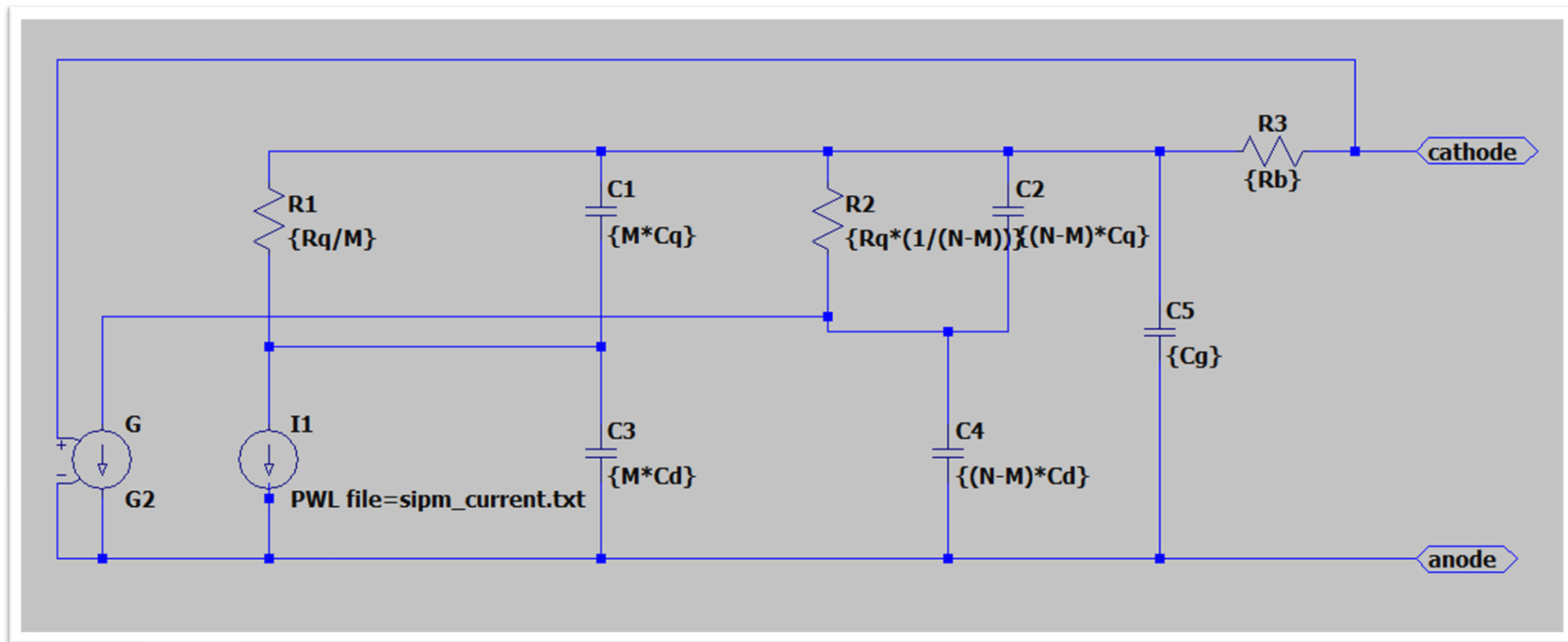
**ESTEBAN CRISTALDO**

March 24th, 2021

# Netlist of the simulation



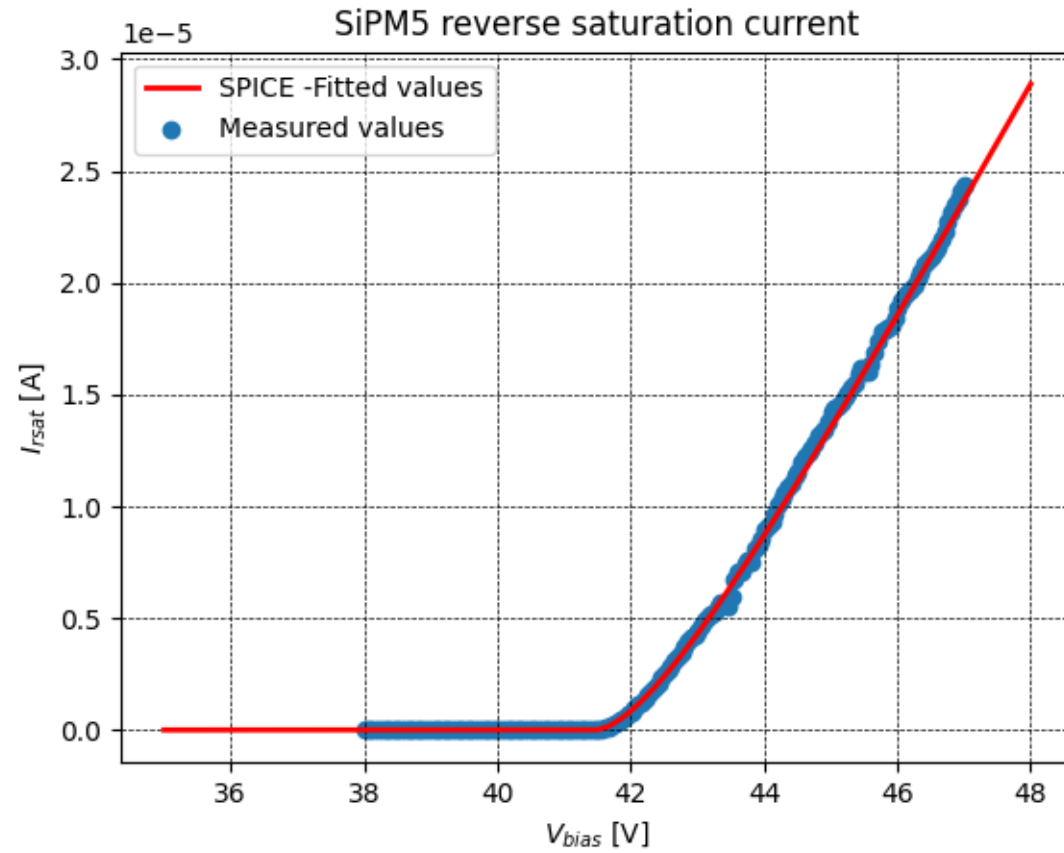
# SiPM model



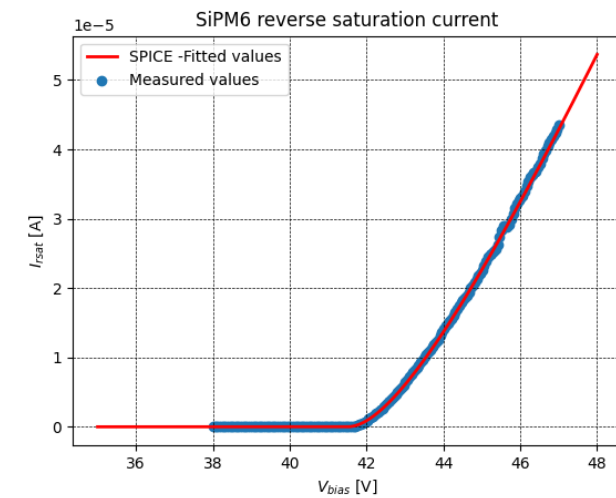
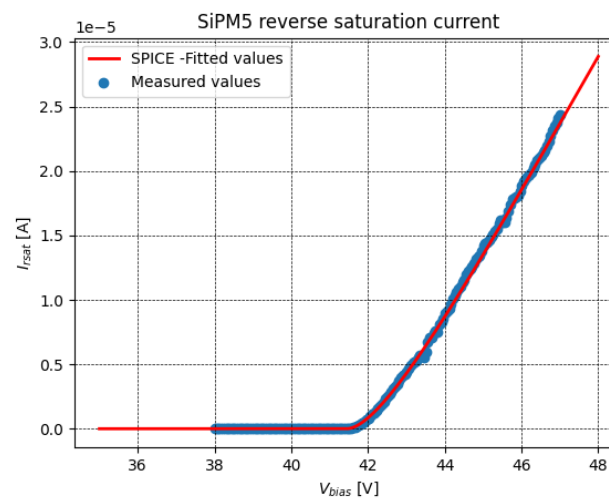
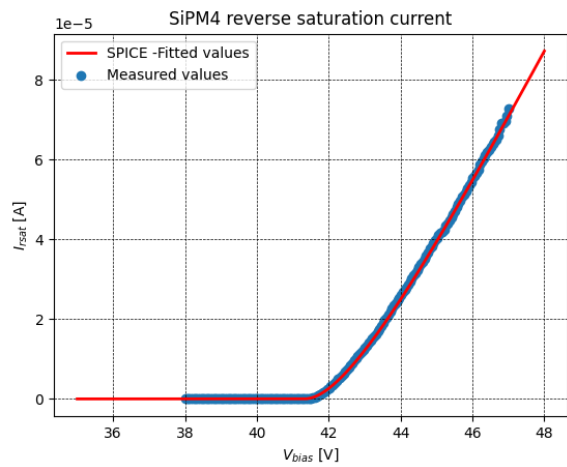
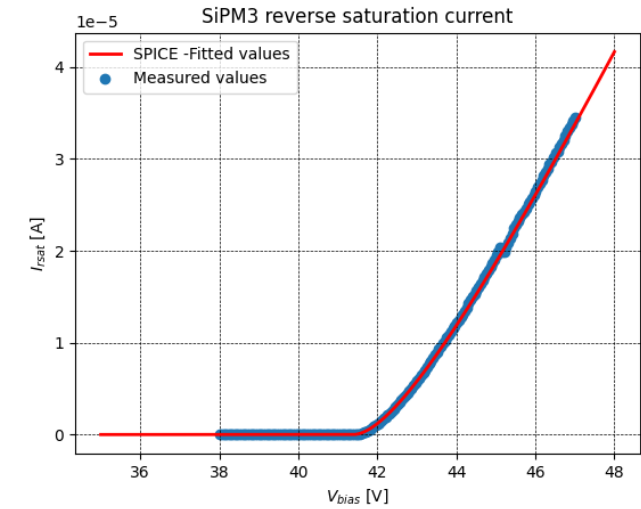
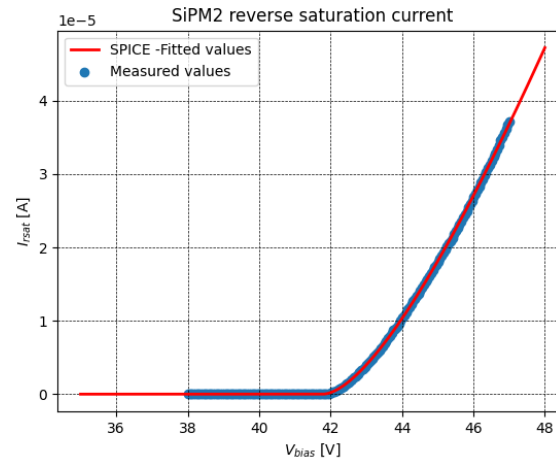
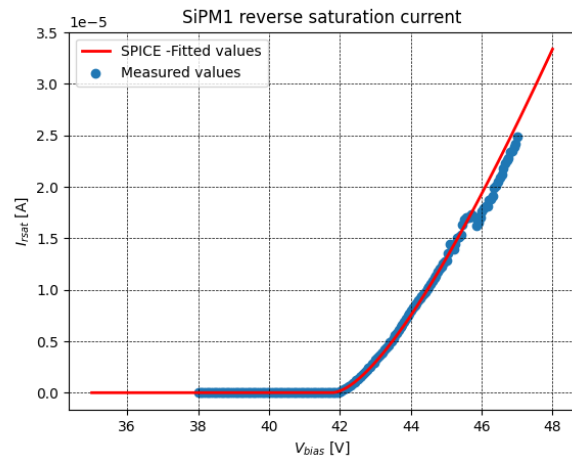
# SiPM model

	Hamamatsu				FBK	
	LR-50	HR-50	LR-75	HR-75	CRYO	TripleT
	...-9932	...-9933	...-9934	...-9935	(DS?)	
Cell size	50	50	75	75	30	50
Cell num	14331	14331	6364	6364	37312	11188
Cap/cell	8,9E-14	8,9E-14	2,0E-13	2,0E-13	5,36E-14	1,79E-13
Res/cell	1,00E+06	3,51E+06	5,00E+05	3,51E+06	3,36E+06	3,02E+06

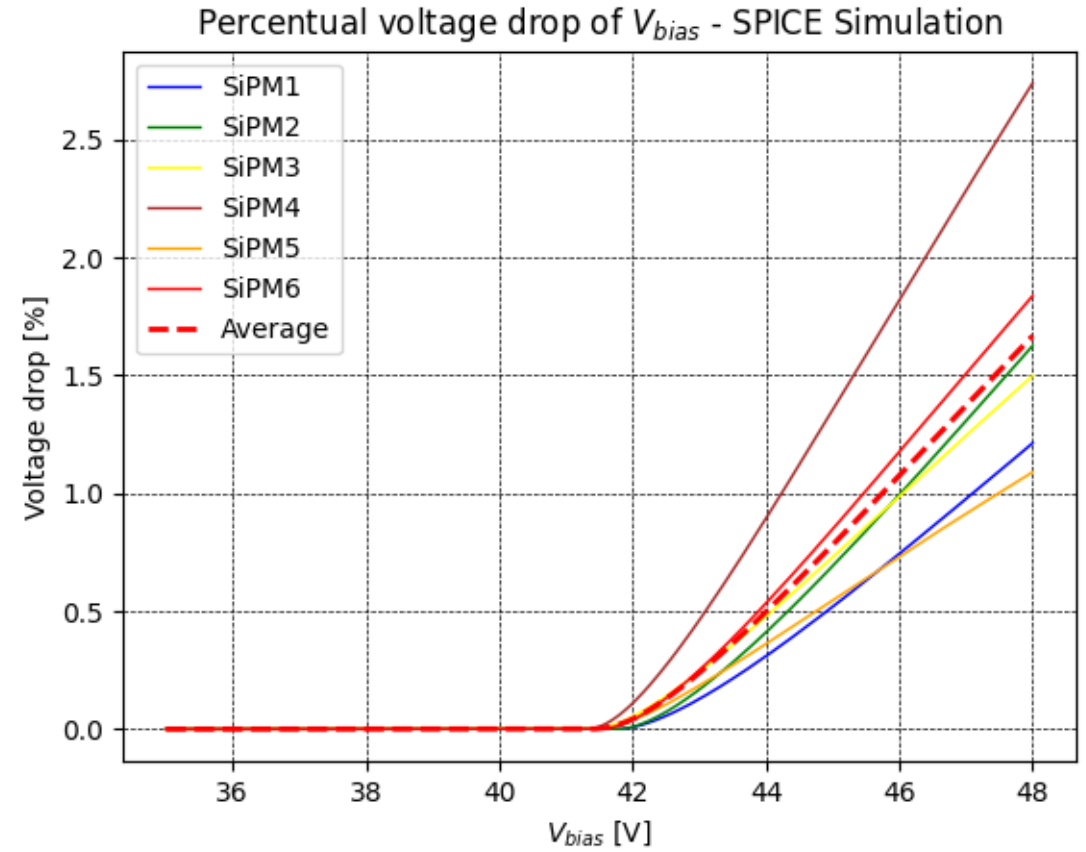
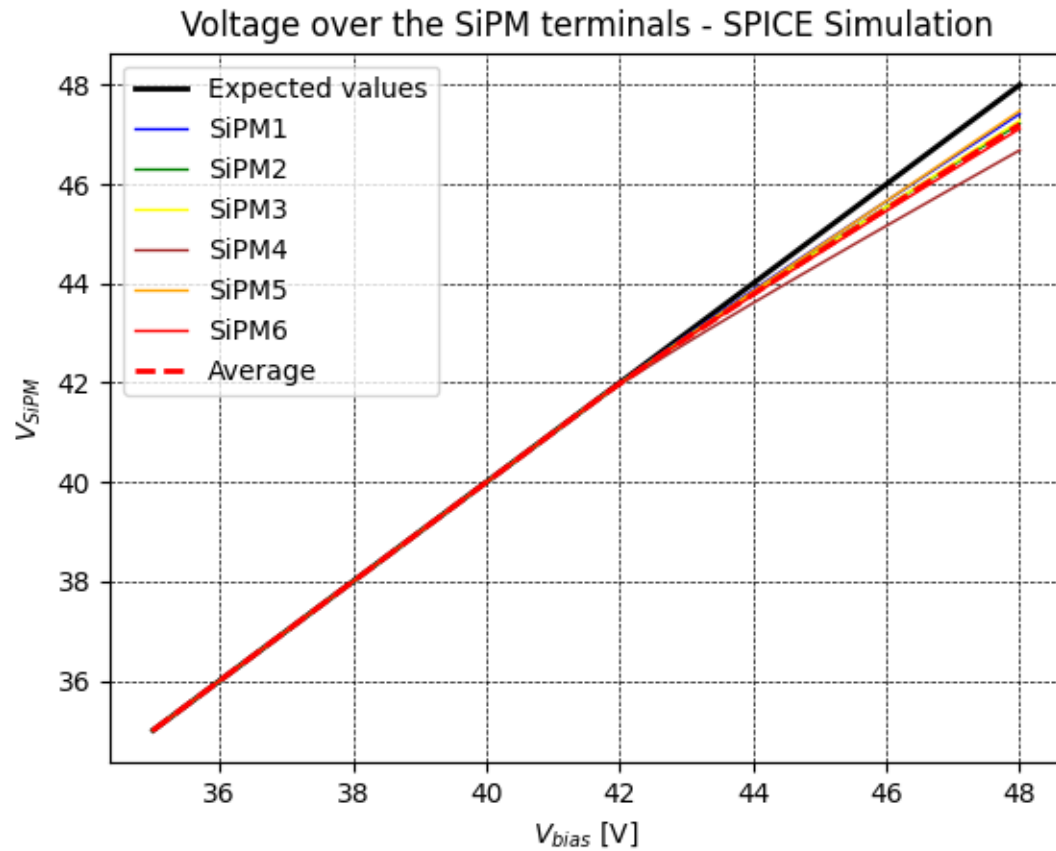
# SiPM reverse saturation current



# SiPM reverse saturation current

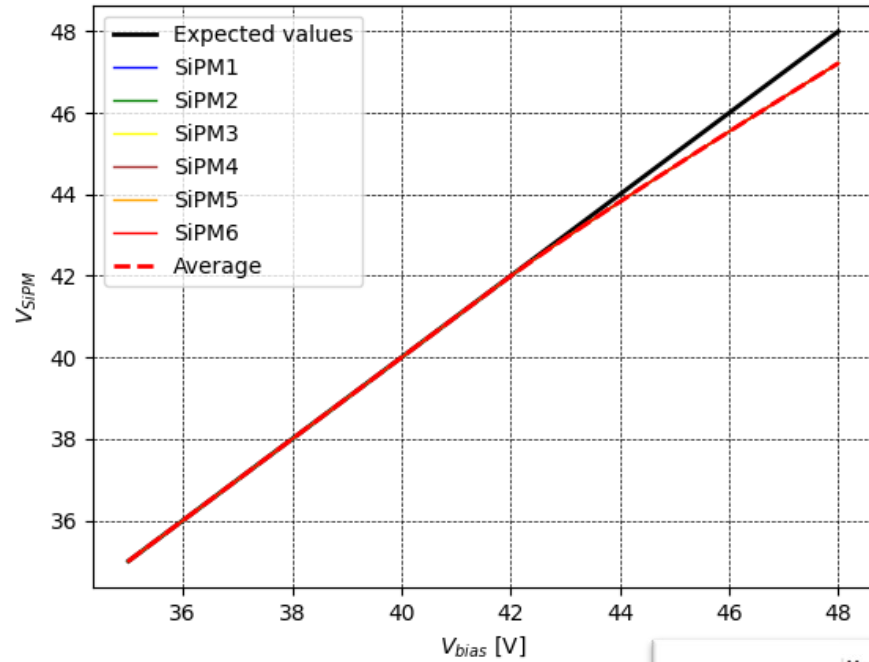


# Simulation using $R = 10\text{ k}\Omega$

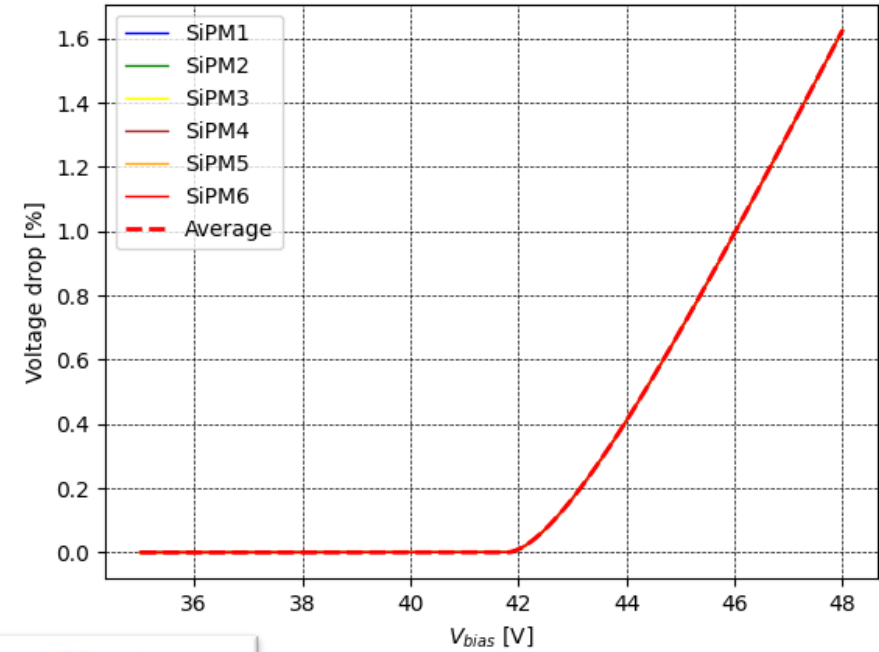


# Simulation using the same profile over different SiPMs

Voltage over the SiPM terminals - SPICE Simulation



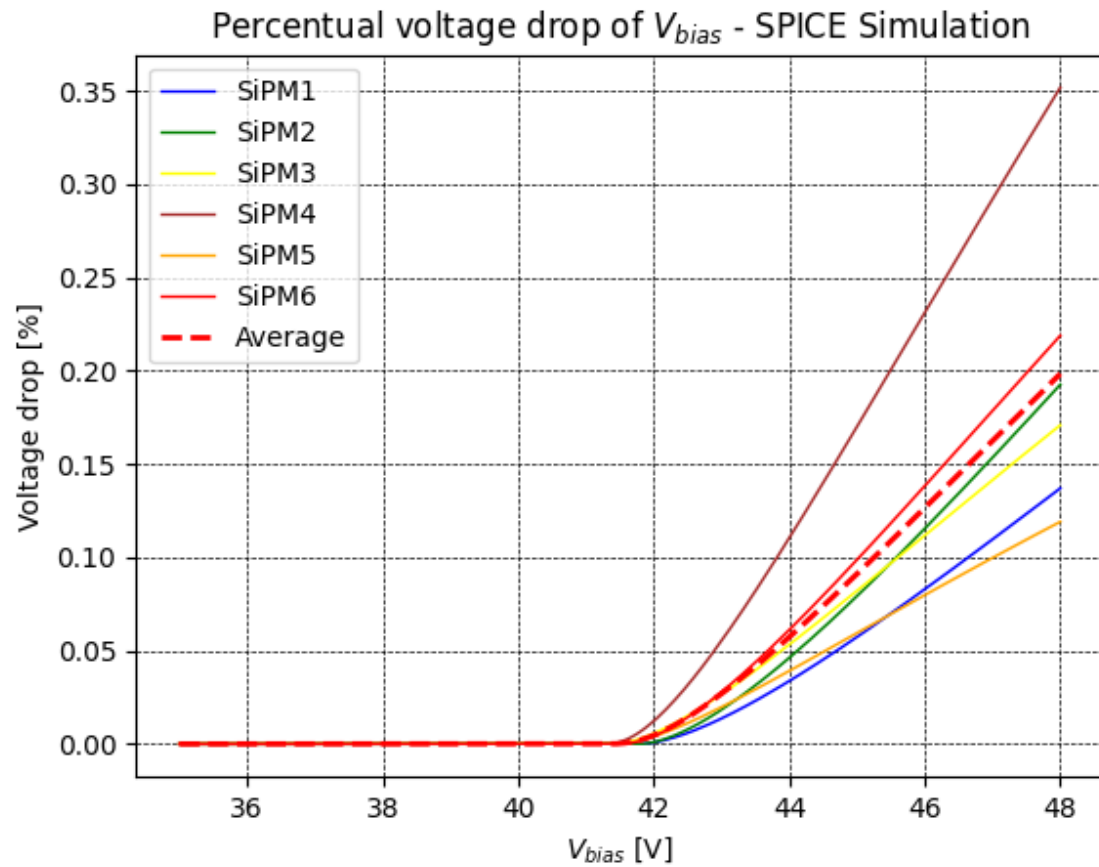
Percentual voltage drop of  $V_{bias}$  - SPICE Simulation



	Hamamatsu				FBK	
	LR-50	HR-50	LR-75	HR-75	CRYO (DS?)	TripleT
	...-9932	...-9933	...-9934	...-9935		
Cell size	50	50	75	75	30	50
Cell num	14331	14331	6364	6364	37312	11188
Cap/cell	8,9E-14	8,9E-14	2,0E-13	2,0E-13	5,36E-14	1,79E-13
tes/cell	1.00E+06	3,51E+06	5,00E+05	3,51E+06	3,36E+06	3,02E+06



# Simulation using $R = 1 \text{ k}\Omega$



- Use the lowest value of  $R$  possible.
- The internal components of the SiPM contribution in the voltage drop is negligible.